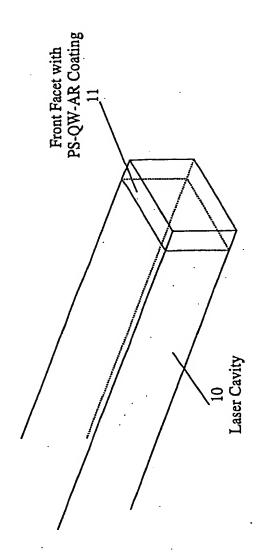
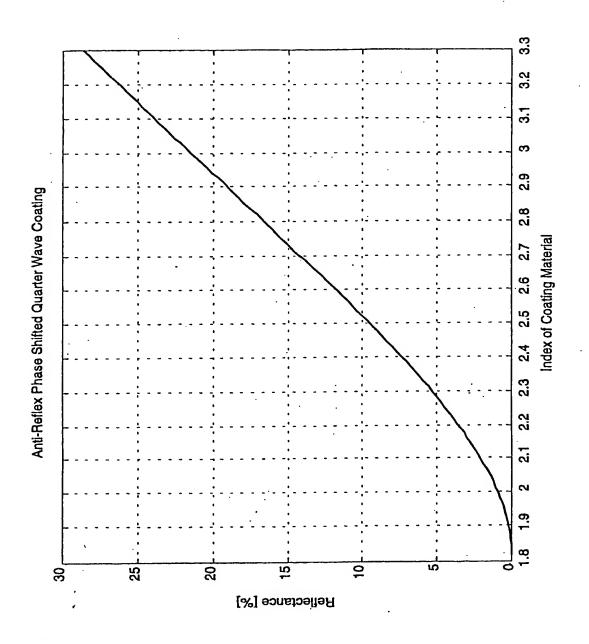


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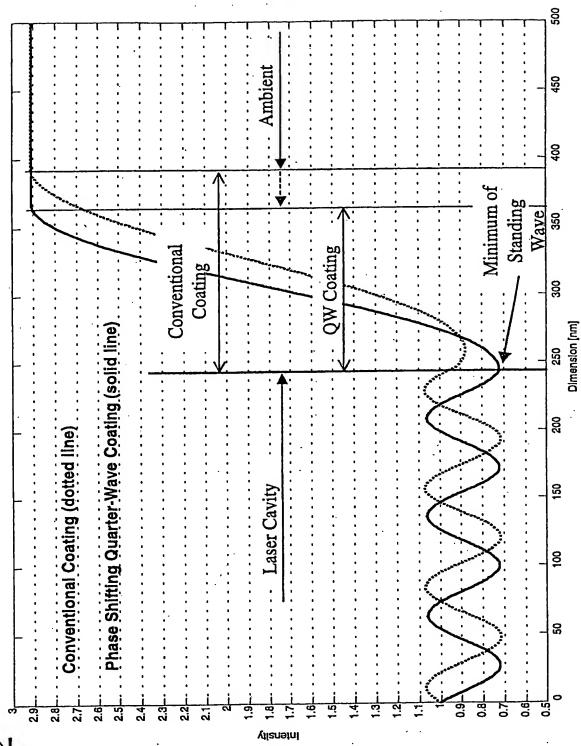


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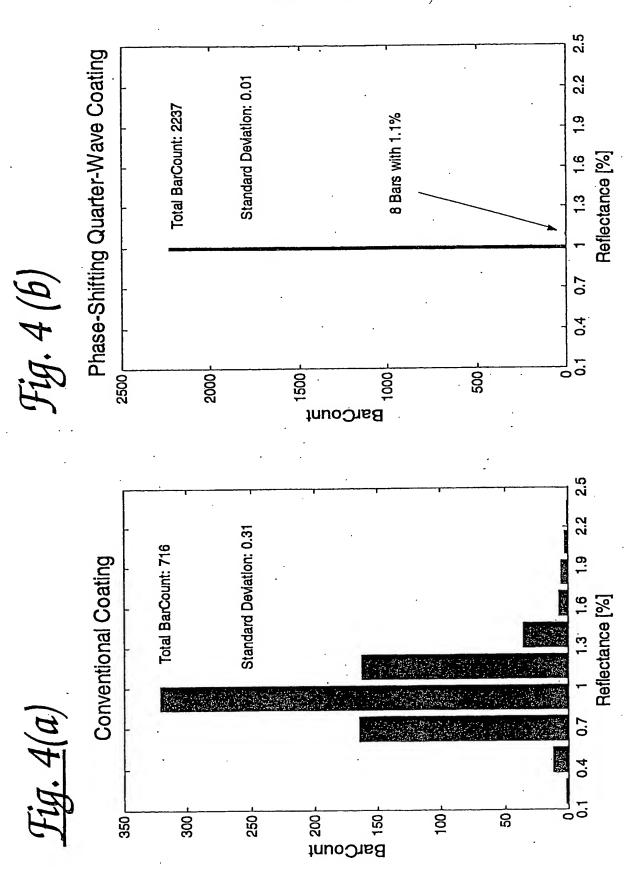


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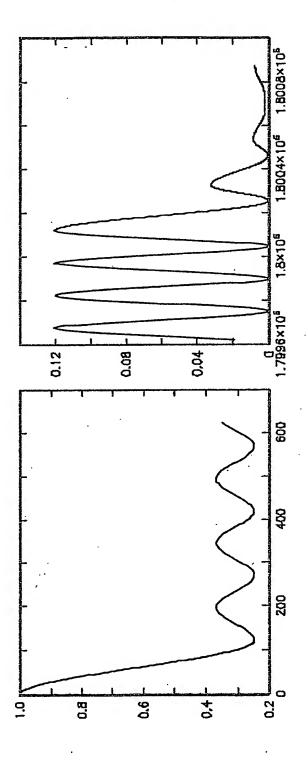




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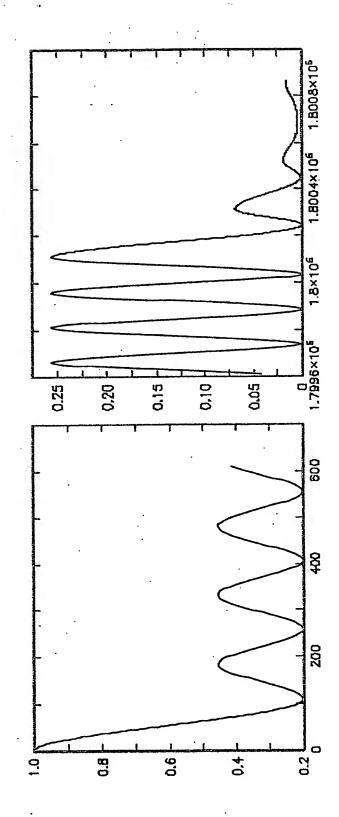


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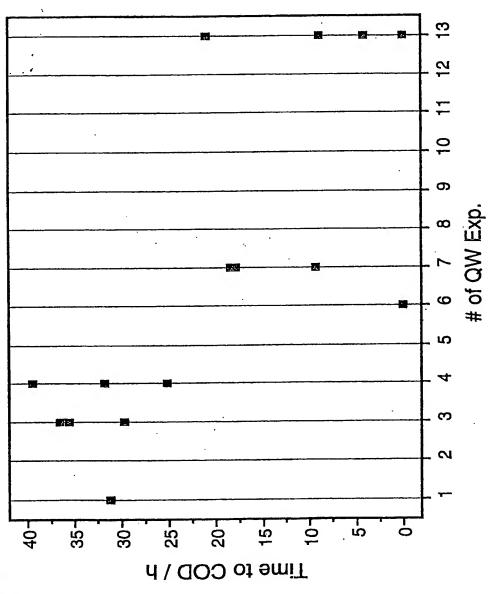
Phase Shifting Quarter Wave Coating with a 1 % Reflectance

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Phase Shifting Quarter Wave Coating with a 4 % Reflectance

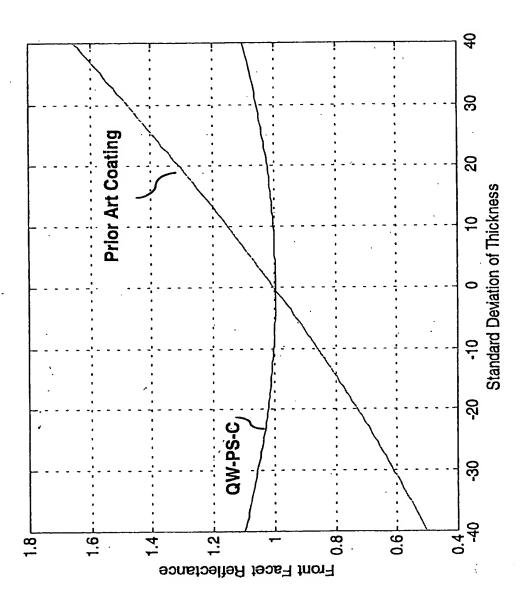
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Time to COD vs. # of QW Exp



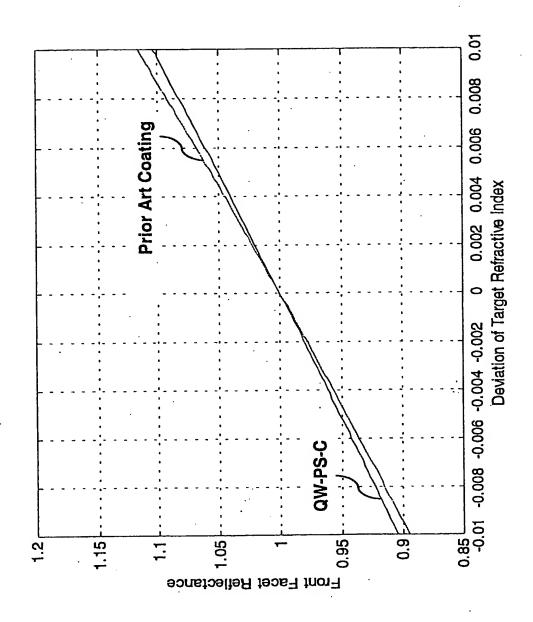
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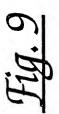
Dependence of reflectance on thickness variation



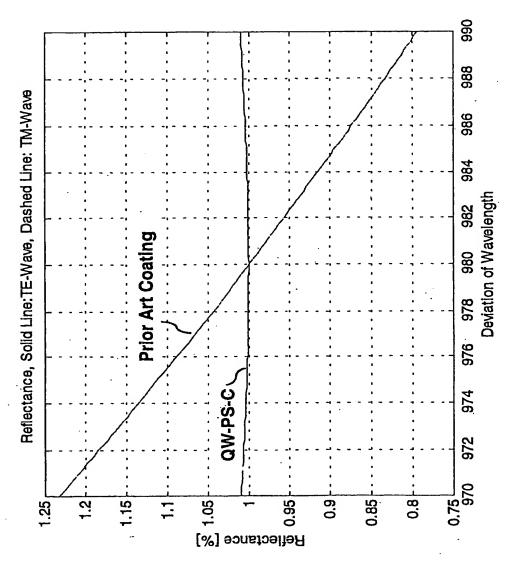
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Dependence of Reflectance on index variation



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Dependence of reflectance on wavelength variation

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Process parameters

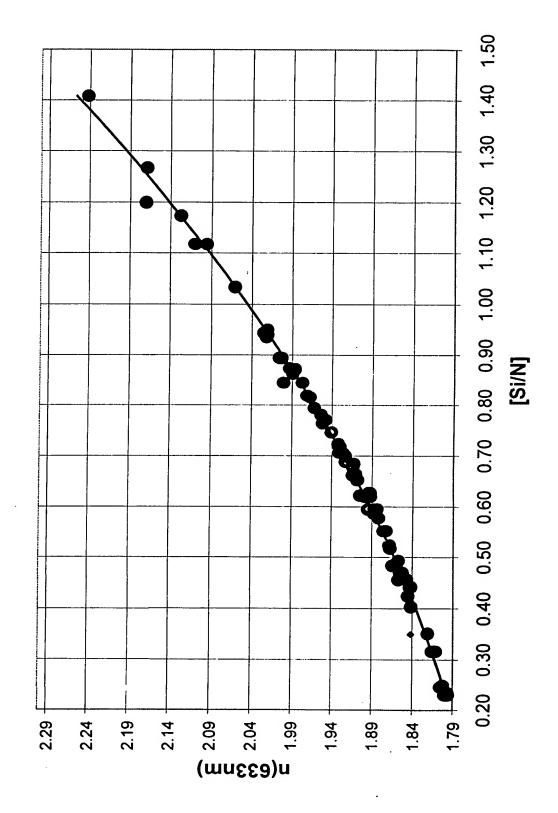
silane flux(* <i>n <sub>ISiH4]</sub> (Sccn</i>	236	403	491	300
ammonia flux n <sub>[NH3]</sub> (sccm)	18	13	8.5	11.2
nitrogen flux n pvzj (sccm)	35	35	35	330
Plasma Power $L_{\text{plasma}}(W)$	25	25	25	20
Pressure P (Torr)	1.4	1.4	1.4	1.4
Reflectivity index of refraction Substrate Temperature Pressure Plasma Power nitrogen flux ammonia flux $T_{\rm S}$ (°C) $P$ (Torr) $L_{\rm plasma}$ (W) $n_{\rm [N/2]}$ (sccm) $n_{\rm [N/3]}$ (sccm)	300	300	300	300
index of refraction n	1.86	2.01	2.23	1.83
Reflectivity R	0.05%	1%	4%	1%(**)

(\*) precursor gas of 2% SiH4 diluted in Helium (\*\*) conventional non- $\lambda/4$  coating

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